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May 2017

H11A1M 6-Pin General Purpose Phototransistor Optocoupler

Features

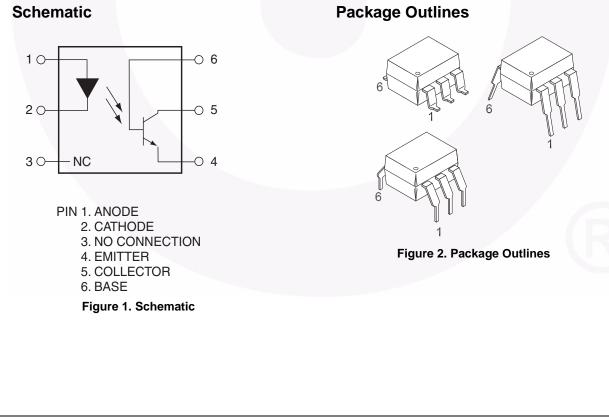
- Minimum Current Transfer Ratio, 50 % at I_F = 10 mA, V_{CE} = 10 V
- Safety and Regulatory Approvals:
 - UL1577, 4,170 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

Applications

- Power Supply Regulators
- Digital Logic Inputs
- Microprocessor Inputs

Description

The general purpose optocoupler consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a standard plastic six-pin dual-in-line package.



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Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–IV
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
M	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V _{peak}
V _{PR}	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1594	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	850	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
Τ _S	Case Temperature ⁽¹⁾	175	°C
I _{S,INPUT}	Input Current ⁽¹⁾	350	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	800	mW
R _{IO}	Insulation Resistance at T _S , V_{IO} = 500 V ⁽¹⁾	> 10 ⁹	Ω

Note:

1. Safety limit values - maximum values allowed in the event of a failure.

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Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Value	Unit
TOTAL DEV	ICE		
T _{STG}	Storage Temperature	-40 to +125	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
TJ	Junction Temperature	-40 to +125	٥C
T _{SOL}	Lead Solder Temperature	260 for 10 seconds	°C
Р	Total Device Power Dissipation @ $T_A = 25^{\circ}C$	270	mW
PD	Derate Above 25°C	2.94	mW/°C
EMITTER			
۱ _F	DC/Average Forward Input Current	60	mA
V _R	Reverse Input Voltage	6	V
l _F (pk)	Forward Current – Peak (300 µs, 2% Duty Cycle)	3	А
P	LED Power Dissipation @ T _A = 25°C	120	mW
PD	Derate Above 25°C	1.41	mW/°C
DETECTOR			
V _{CEO}	Collector-to-Emitter Voltage	30	V
V _{CBO}	Collector-to-Base Voltage	70	V
V _{ECO}	Emitter-to-Collector Voltage	7	V
D	Detector Power Dissipation @ T _A = 25°C	150	mW
PD	Derate Above 25°C	1.76	mW/°C

3

Electrical Characteristics

 $TA = 25^{\circ}C$ unless otherwise specified.

Individual Component Characteristics

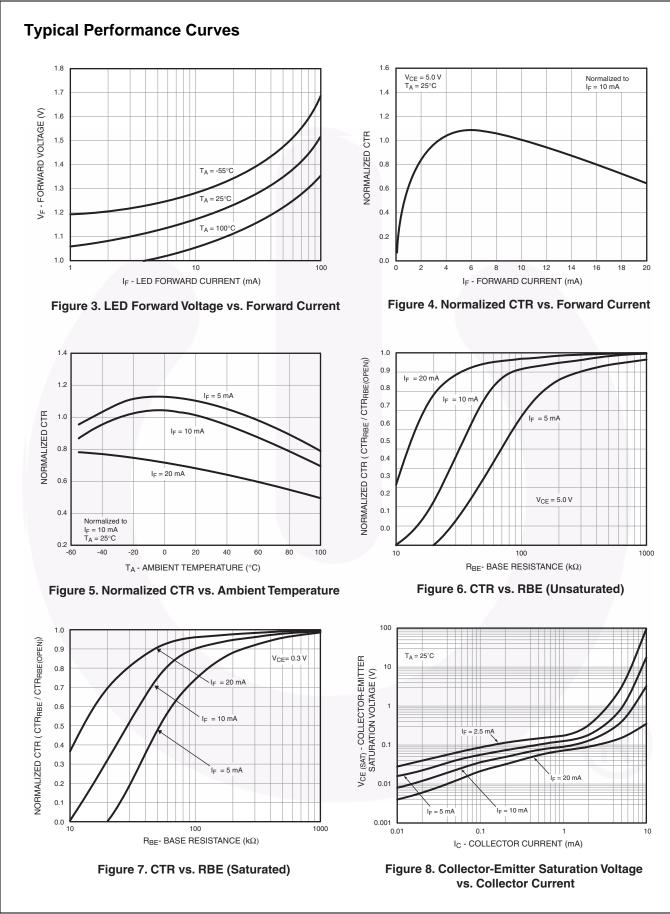
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER						
V _F	Input Forward Voltage	I _F = 10 mA		1.18	1.50	V
I _R	Reverse Leakage Current	V _R = 6.0 V		0.001	10	μA
DETECTOR						
BV _{CEO}	Collector-to-Emitter Breakdown Voltage	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm F} = 0$	30	100		V
BV _{CBO}	Collector-to-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, \ I_{F} = 0$	70	120		V
BV _{ECO}	Emitter-to-Collector Breakdown Voltage	$I_{E} = 100 \ \mu A, I_{F} = 0$	7	10		V
I _{CEO}	Collector-to-Emitter Dark Current	$V_{CE} = 10 \text{ V}, \text{ I}_{F} = 0$		1	50	nA
I _{CBO}	Collector-to-Base Dark Current	V _{CB} = 10 V			20	nA
C _{CE}	Capacitance	$V_{CE} = 0 V, f = 1 MHz$		8		pF

Transfer Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
DC CHAR	DC CHARACTERISTICS					
CTR	Current Transfer Ratio,Collector-to- Emitter	$I_{\rm F}$ = 10 mA, $V_{\rm CE}$ = 10 V	50			%
V _{CE(SAT)}	Collector-to-Emitter Saturation Voltage	$I_{\rm C} = 0.5 \text{ mA}, I_{\rm F} = 10 \text{ mA}$			0.4	V
AC CHAR	AC CHARACTERISTICS					
T _{ON}	Non-Saturated Turn-on Time	$I_{F} = 10 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_{L} = 100 \Omega \text{ (Figure 13)}$		2		μs
T _{OFF}	Turn-off Time	$I_F = 10$ mA, $V_{CC} = 10$ V, R _L = 100 Ω (Figure 13)		2		μs

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{ISO}	Input-Output Isolation Voltage	t = 1 Minute	4170			VAC _{RMS}
C _{ISO}	Isolation Capacitance	V _{I-O} = 0 V, f = 1 MHz		0.2		pF
R _{ISO}	Isolation Resistance	$V_{I-O} = \pm 500 \text{ VDC},$ $T_A = 25^{\circ}\text{C}$	10 ¹¹			Ω

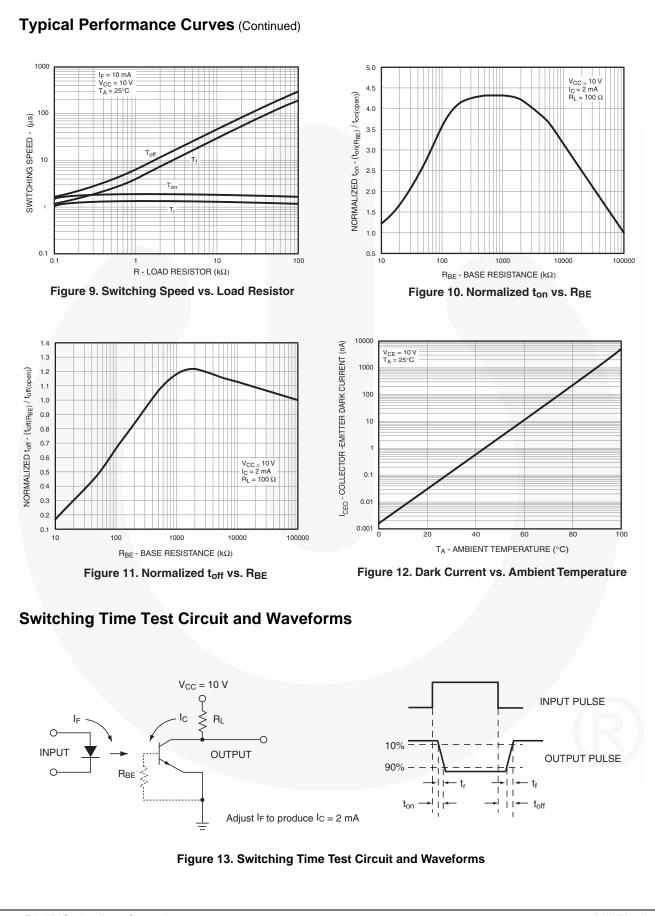


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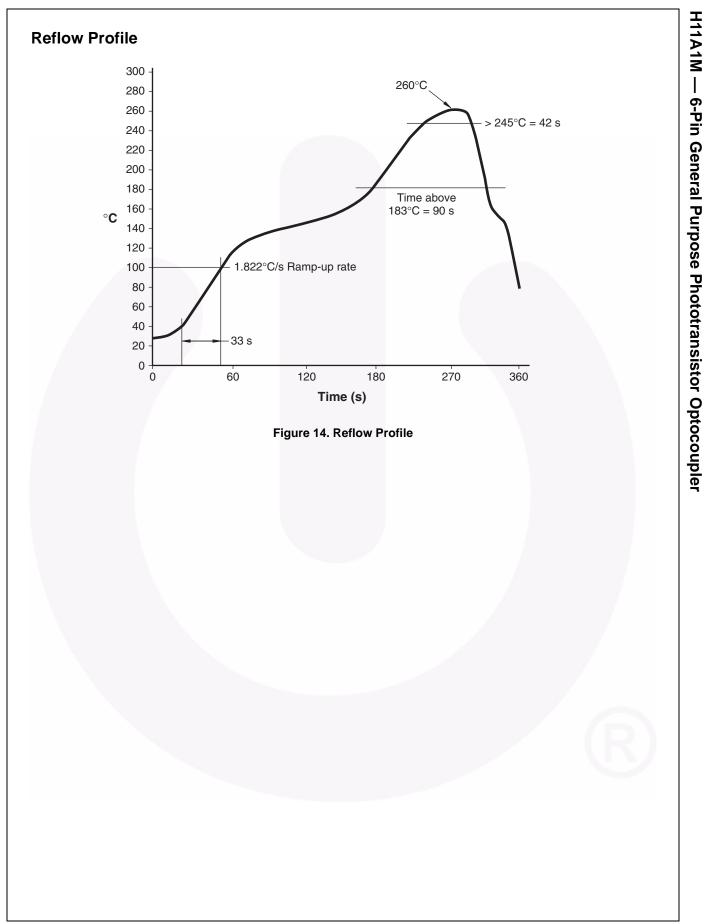
H11A1M Rev. 1.1

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Part Number	Package	Packing Method
H11A1M	DIP 6-Pin	Tube (50 Units)
H11A1SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
H11A1SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
H11A1VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
H11A1SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
H11A1SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
H11A1TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

Marking Information

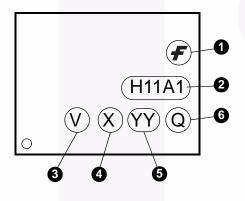
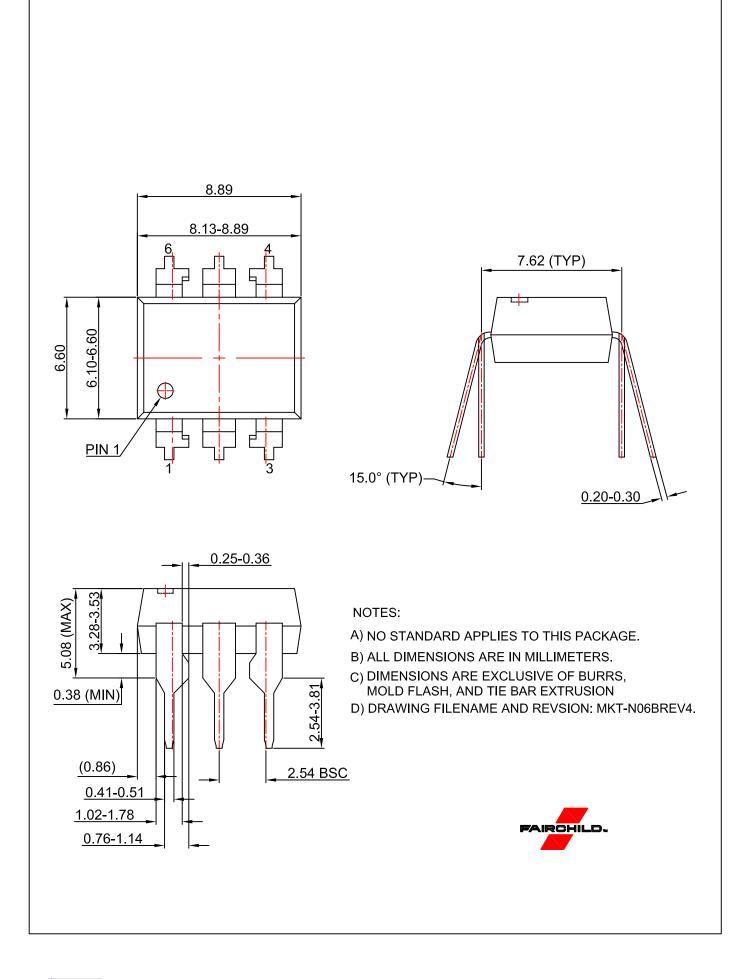
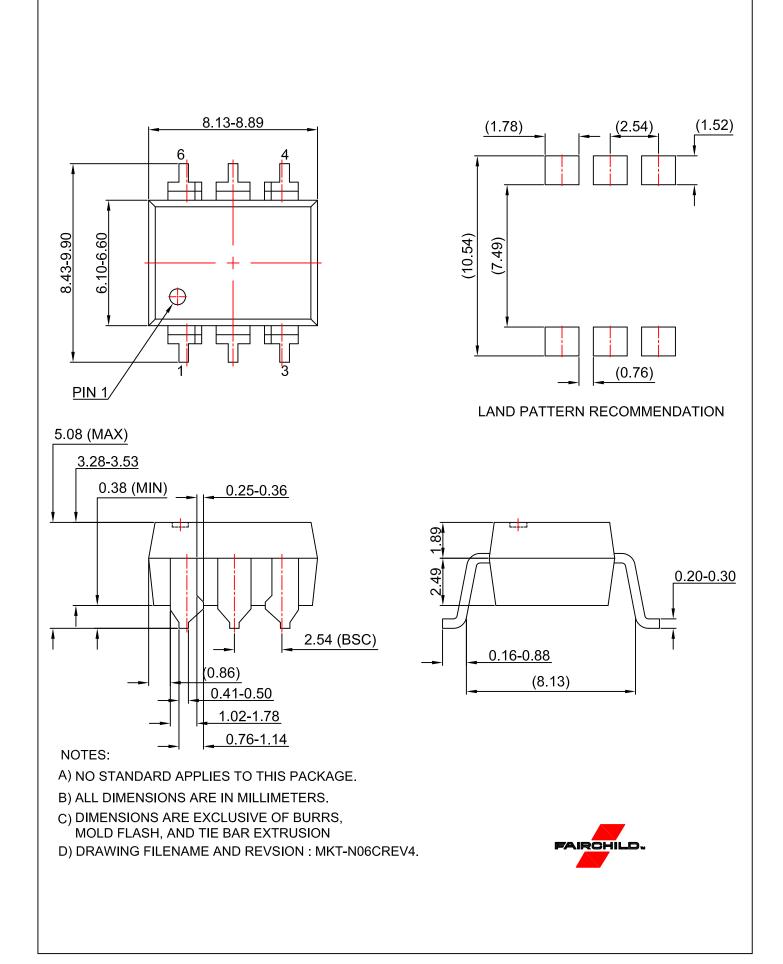


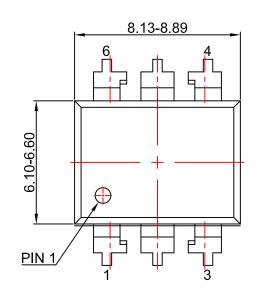
Figure 15. Top Mark

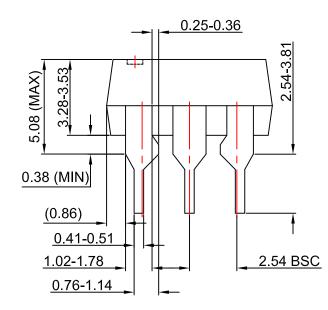
Table 1. Top Mark Definitions

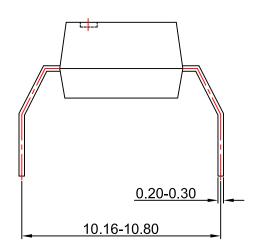
1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "6"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code











NOTES:

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